Market News

Infineon launches CoolGaN™ 600 V GIT HEMT portfolio, delivering exceptional performance and quality, in full supply

Munich, Germany – 5 May, 2023 – Infineon Technologies AG (FSE: IFX / OTCQX: IFNNY) has successfully integrated the CoolGaN™ 600 V hybrid-drain-embedded gate injection transistor (HD-GIT) technology into its in-house manufacturing. The company is now releasing the complete portfolio of its high-quality GaN devices to the broader market. Taking advantage of Infineon's fully owned and controlled supply chain, the expanded GaN portfolio includes a wide range of discrete and fully integrated GaN devices that far exceed JEDEC lifetime requirements. The new CoolGaN devices have been optimized for various applications ranging from industrial SMPS for servers, telecom, and solar to consumer applications, such as chargers and adapters, motor drives, TV/monitor, and led lighting systems.

The portfolio of CoolGaN discrete and integrated power stage (IPS) devices provides designers with the necessary flexibility to meet their specific needs for industrial applications complying with JEDEC standards (JESD47 and JESD22). The discrete CoolGaN GIT HEMT devices are available in DSO-20-85, DSO-20-87, HSOF-8-3, LSON-81-, and TSON-8 packages and in multiple on-state resistance ($R_{DS(on),max}$) values ranging from 42 to 340 mΩ. The IPS solutions come in the form of half-bridge and single-channel devices. Half-bridge solutions integrate two GaN switches and are housed in a TIQFN-28 package with $R_{DS(on),max}$ values of (2x) 190-650 mΩ. Single-channel solutions are available in a thermally-enhanced TIQFN-21 package with $R_{DS(on),max}$ values in the range of 130-340 mΩ.

Infineon's CoolGaN GIT technology features a unique combination of a robust gate structure, internal electrostatic discharge (ESD) protection, and excellent dynamic $R_{DS(on)}$ performance. It fully exploits the intrinsic properties of GaN to deliver exceptional figures of merit (FoM) compared to Si technology, such as ten times higher breakdown field, two times higher electron mobility, ten times lower output charge, zero reverse recovery charge, and ten times lower gate charge with linear output capacitance (C_{OSS}).

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These technical features provide significant design advantages such as very low $R_{DS(on)}$, improved efficiency in resonant circuits, the use of new topologies and current modulation, as well as fast and nearly lossless switching.

Infineon's range of CoolGaN 600 V GIT discrete devices includes both top- and bottom-side cooled (TSC/BSC) JEDEC-compliant packages. CoolGaN TSC power packages are unique in the market and address higher power requirements. The benefits for designers are manifold, ultimately leading to compact and lightweight products with high power density, improved energy efficiency, and reduced total system costs. Infineon's commitment to quality standards ensures unmatched robustness and long-term reliability, lowering operating and maintenance costs for high-energy consumption applications.

Availability

Infineon's CoolGaN devices are in volume production, samples can be ordered now. More information is available at www.infineon.com/coolgan. The CoolGaN™ 600 V GIT HEMT portfolio will be showcased at PCIM Europe 2023.

Infineon at the PCIM 2023

At the PCIM Europe 2023 tradeshow, Infineon is showcasing innovative product-to-system solutions for applications that will power the world and shape the future. Company representatives will also be giving several presentations at the accompanying PCIM Conference and Industry & E-Mobility Forum with live and on-demand video presentations, followed by discussions with the speakers. "Driving decarbonization and digitalization. Together." at the Infineon booth #412 in hall 7, 9-11 May, 2023 in Nuremberg/Germany. Information about the PCIM Europe 2023 show highlights is available at www.infineon.com/pcim.

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